

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

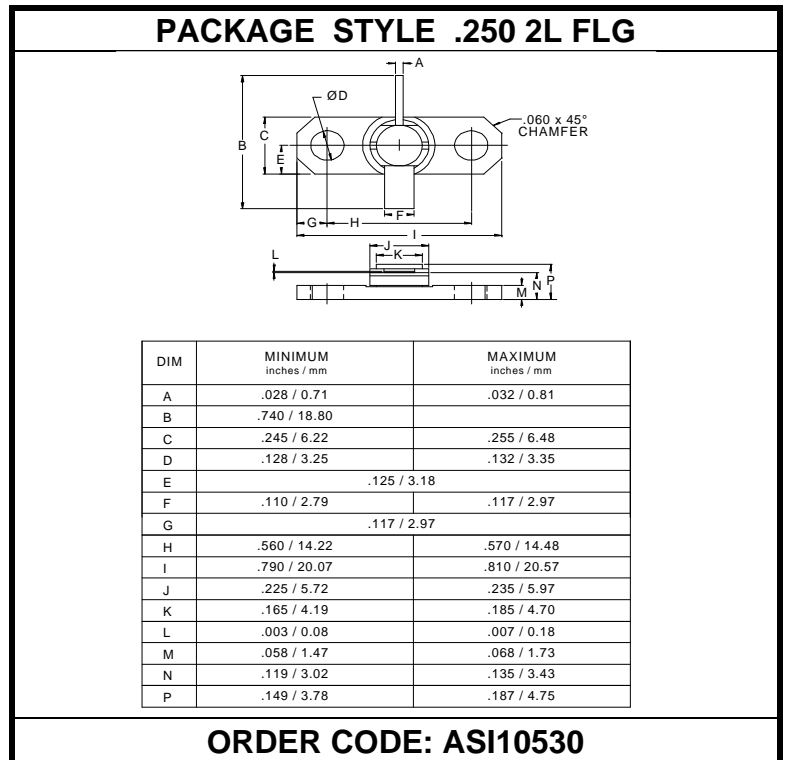
The **ASI 2010** is Designed for General Purpose Class C Power Amplifier Applications up to 2300 MHz.

**FEATURES:**

- $P_G = 5$  dB min. at 10 W/ 2,000 MHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.5 A
$V_{CC}$	35 V
$P_{DISS}$	35 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+200^\circ C$
$\theta_{JC}$	5.0 $^\circ C/W$


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 5$ mA	45			V
$BV_{CER}$	$I_C = 15$ mA $R_{BE} = 10 \Omega$	45			V
$BV_{EBO}$	$I_E = 1$ mA	3.5			V
$I_{CBO}$	$V_{CB} = 28$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1000$ mA	15		120	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			7.5	pF
$P_G$	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 2.0$ GHz	5.0			dB
$\eta_c$		35			%